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(54) Title: PROCESS FOR FABRICATING AN ELECTRONIC DEVICE

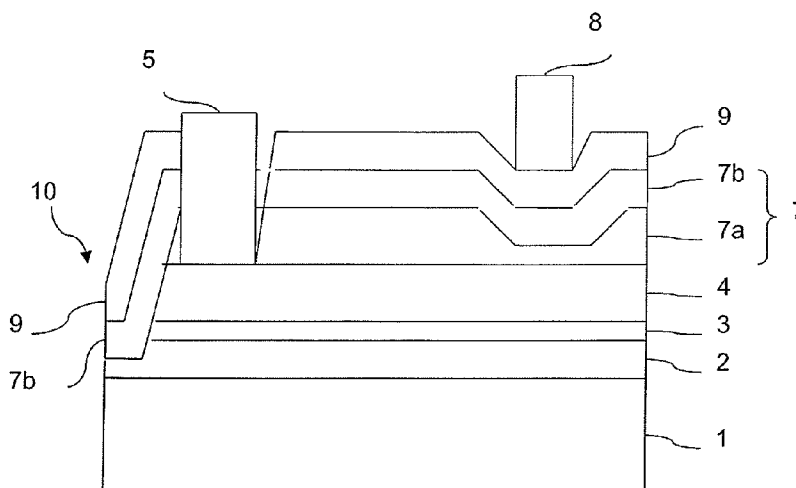


FIG. 3D

(57) Abstract: The present invention concerns an electronic device made of group III/N materials and a method of fabricating thereof, comprising the growth by epitaxy on a substrate layer (1) of the following successive layers: - a layer (2, 3) adapted to contain an electron gas; - a barrier layer (4); and - a surface layer (7a), the process also including an etching step for at least part of the surface layer (7a). After the etching step, an epitaxial regrowth is performed so as to grow a covering layer (7b) on the etched surface layer (7a). The material of the surface layer, (7a) and the material of the covering layer (7b) include at least one Group III element and nitrogen.

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